ABSTRACT OF THE DISCLOSURE

A semiconductor device which is capable of suppressing short-circuit currents caused to flow through defective areas in a first semiconductor layer can be manufactured at high yield, by utilizing a method of manufacturing a semiconductor device including the steps of forming a first semiconductor layer on a substrate, forming a first transparent electroconductive layer on the first semiconductor layer, and forming a second semiconductor layer on the first transparent electroconductive layer, the method further including executing passivation treatment on defects in the first semiconductor layer before the formation of the second semiconductor layer.